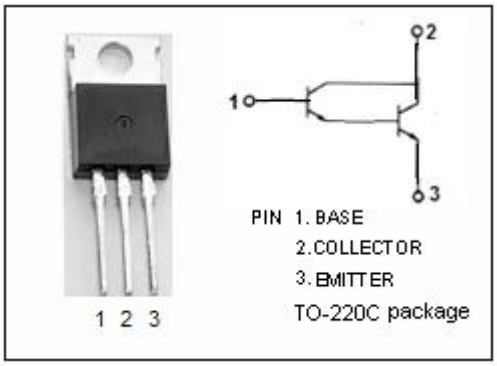
isc Silicon NPN Darlington Power Transistor — 2SD1128

DESCRIPTION

- Excellent linearity in h_{FE}
- High DC Current Gain
- High Reliability
- Excellent Safe Operating Area
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

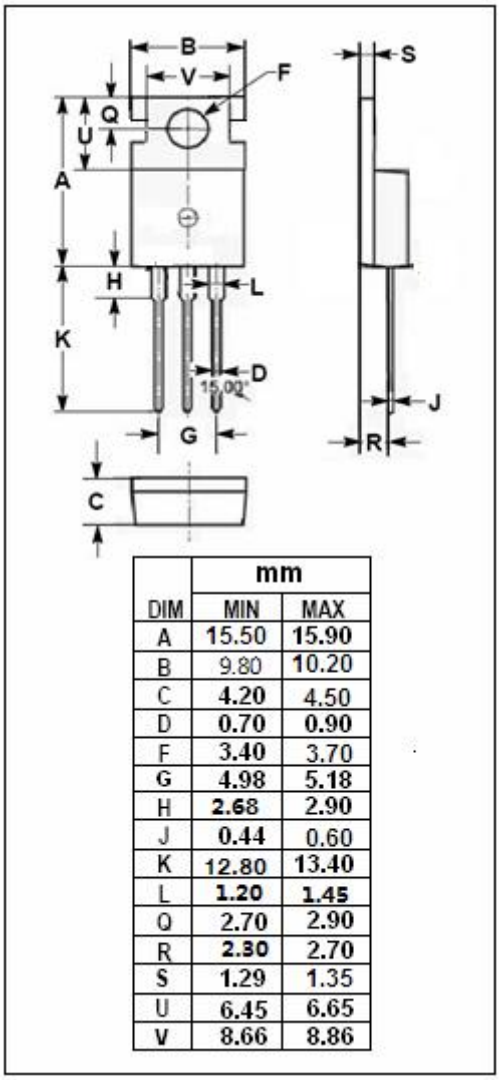
- Color & B/W TV power
- supply Active power filter
- Industrial use power supply (series regulator)
- General purpose power amplifiers

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_B	Base Current-Continuous	0.5	A
P_C	Collector Power Dissipation @ T_C=25℃	30	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	4.1	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector- Base Breakdown Voltage	I_C= 1mA ; I_E= 0	150			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA ; I_B= 0	100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1.5A; I_B= 50mA			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 1.5A; I_B= 50mA			2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 150V; I_E= 0			1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}=6V; I_C=0			1	mA
h_{FE}	DC Current Gain	I_C= 1A; V_{CE}= 4V	700			